

Docket No.: 60188-731

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
	:	
Yutaka HIROSE, et al.	:	Confirmation Number:
	:	
Serial No.:	:	Group Art Unit:
	:	
Filed: December 17, 2003	:	Examiner:
	:	
For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME		

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION						ATTY. DOCKET NO. 60188-731		SERIAL NO.			
(PTO-1449)						APPLICANT Yutaka HIROSE, et al.					
						FILING DATE December 17, 2003		GROUP			
U.S. PATENT DOCUMENTS											
EXAMINER'S INITIALS		CITE NO.	Document Number Number-Kind Code ₂ (<i>If known</i>)		Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
			US	6,057,564	05/02/2000	Rennie					
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FOREIGN PATENT DOCUMENTS											
EXAMINER'S INITIALS		CITE NO.	Foreign Patent Document Country Codes - Number 4 - Kind Codes (<i>If known</i>)		Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines Where Relevant Figures Appear	Translation <div>YesNo</div>	
			JP	11-54798	02/26/1999	TOSHIBA CORP.		JAPAN (w/English Abstract)			
			JP	10-223901	08/21/1998	SONY CORP.		JAPAN (w/English Abstract)			
			JP	2000-150792	05/30/2000	AGENCY OF IND SCIENCE & TECHNOL		JAPAN (w/English Abstract)			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)											
EXAMINER'S INITIALS		CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.								
			HASHIZUME, T., et al. "Characterization of GaN and AlGaN Surfaces and Their Insulated Gate Structures." The Institute of Electronics. Information and Communication Engineers. Technical Report of IEICE., ED2002-87, LQE2002-62 (2002-06). Pp. 57-60, June 14, 2002.								
			KUSUNOKI, S., et al. " Hot-Carrier-Resistant Structure by Re-oxidized Nitrided Oxide Sidewall for Highly Reliable and High Performance LDD MOSFETS.", IEEE, IEDM 91, 25.4.1- 25.4.4, pp. 349-652, 1991								
EXAMINER						DATE CONSIDERED					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.